

ABSTRACT

Embodiments of the present disclosure disclose a semiconductor device, an optical device, and a manufacturing method for a semiconductor structure. The
5 manufacturing method includes: forming a stacked structure on a substrate, the stacked structure including a functional layer and a sacrificial layer which are alternately stacked, the functional layer and the sacrificial layer being made of a same material, the sacrificial layer being doped with n-type or p-type impurities, and a doping concentration of the sacrificial layer being greater than a doping concentration of the
10 functional layer; and selectively removing the sacrificial layer from the stacked structure.